DATA SHEET



MOS FIELD EFFECT TRANSISTOR μ PA2211T1M

P-CHANNEL MOS FET FOR SWITCHING

DESCRIPTION

The μ PA2211T1M is P-channel MOS Field Effect Transistor designed for power management applications of portable equipments, such as load switch.

FEATURES

- Low on-state resistance
- RDS(on)1 = 25 mΩ MAX. (VGS = -4.5 V, ID = -7.5 A) RDS(on)2 = 34 mΩ MAX. (VGS = -2.5 V, ID = -3.8 A) RDS(on)3 = 66 mΩ MAX. (VGS = -1.8 V, ID = -3.8 A)
- Built-in gate protection diode
- -1.8 V Gate drive available

ORDERING INFORMATION

PART NUMBER	PACKING	PACKAGE
μΡΑ2211Τ1Μ-Τ1-ΑΤ ^{Νote}	8 mm embossed taping	8-pin VSOF (1629)
μΡΑ2211Τ1Μ-Τ2-ΑΤ ^{Note}	3000 p/reel	0.011 g TYP.

Note Pb-free (This product does not contain Pb in external electrode and other parts.)

ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-12	V
Gate to Source Voltage (VDS = 0 V)	Vgss	∓8	V
Drain Current (DC)	D(DC)	∓7.5	А
Drain Current (pulse) Note1	D(pulse)	∓30	А
Total Power Dissipation Note2	Pt1	1.1	W
Total Power Dissipation (PW = 5 sec) Note2	Pt2	2.5	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

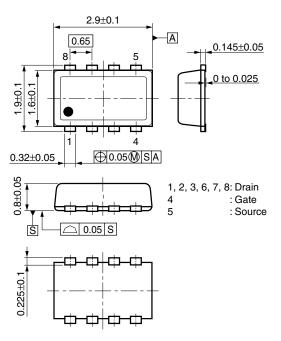
2. Mounted on glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

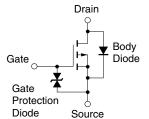
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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PACKAGE DRAWING (Unit: mm)





EQUIVALENT CIRCUIT

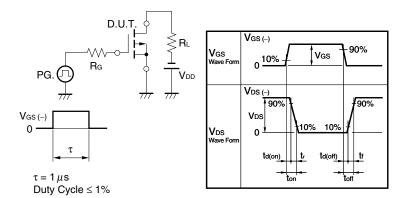
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = -12 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	Igss	V _{GS} = ∓8 V, V _{DS} = 0 V			∓10	μA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-0.45		-1.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = -10 V, I _D = -3.8 A	5			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = -4.5 V, I _D = -7.5 A		21	25	mΩ
	RDS(on)2	V _{GS} = -2.5 V, I _D = -3.8 A		25	34	mΩ
	RDS(on)3	V _{GS} = -1.8 V, I _D = -3.8 A		34	66	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V,		1350		pF
Output Capacitance	Coss	V _{GS} = 0 V,		255		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		215		pF
Turn-on Delay Time	td(on)	V _{DD} = -10 V, I _D = -3.8 A,		10.7		ns
Rise Time	tr	V _{GS} = -4.0 V,		16.7		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		101.0		ns
Fall Time	tr			76.4		ns
Total Gate Charge	QG	V _{DD} = -9.6 V,		14.9		nC
Gate to Source Charge	QGS	V _{GS} = -4.5 V,		2.8		nC
Gate to Drain Charge	Qgd	I _D = -7.5 A		4.0		nC
Body Diode Forward Voltage Note	VF(S-D)	I⊧ = –7.5 A, V₀s = 0 V		0.88	1.2	V
Reverse Recovery Time	trr	I⊧ = –7.5 A, V₀s = 0 V,		60		ns
Reverse Recovery Charge	Qrr	di/dt = -47 A/ <i>µ</i> s		19		nC

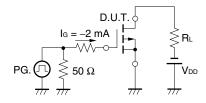
ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

Note Pulsed

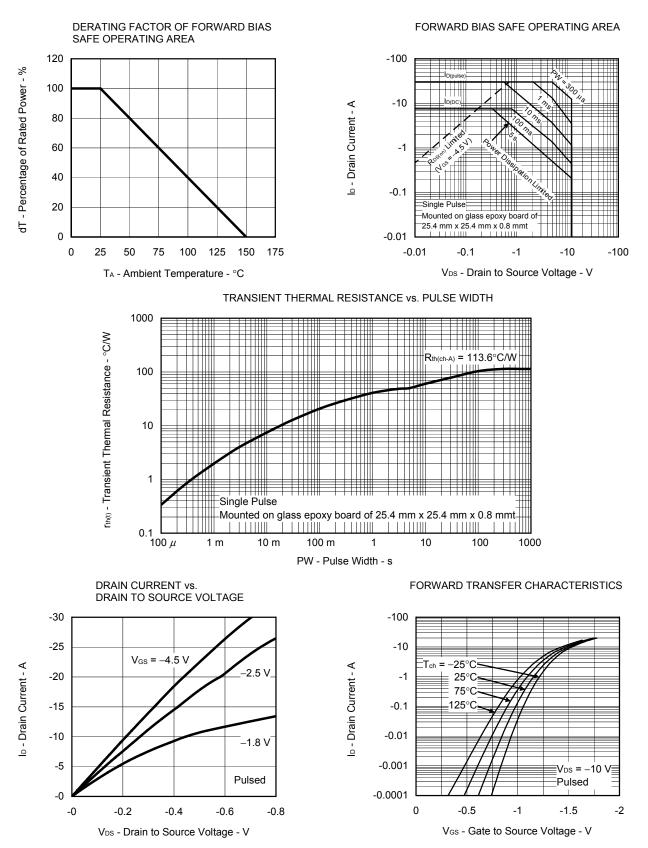
TEST CIRCUIT 1 SWITCHING TIME



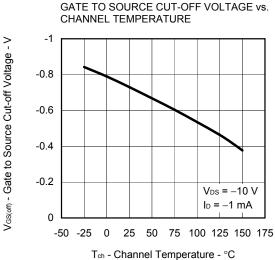
TEST CIRCUIT 2 GATE CHARGE

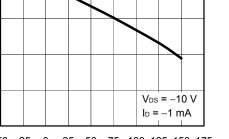


TYPICAL CHARACTERISTICS (T_A = 25°C)

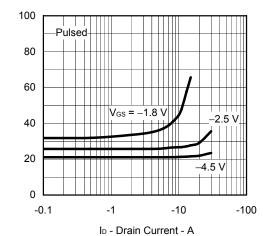


Data Sheet G19452EJ1V0DS

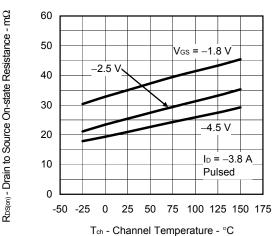




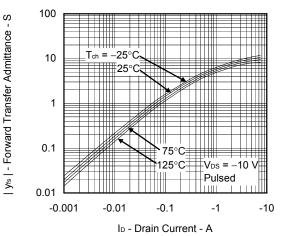




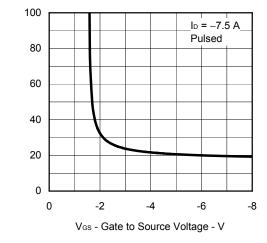
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



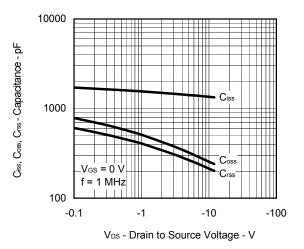
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



Data Sheet G19452EJ1V0DS

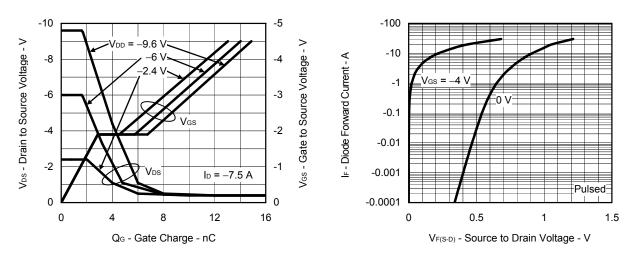
 $R_{DS(on)}$ - Drain to Source On-state Resistance - $m\Omega$

 $R_{DS(on)}$ - Drain to Source On-state Resistance - m Ω

NEC

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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